



Bipolar NPN Bare Die – BTN6032

Part Description

The BTN6032 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 80V
- VCEO = 80V
- VEBO = 7V
- hFE = 150- @ VCE = 1V, IC = 0.01A
- VCE(Sat) = 0.25V @ IC = 0.1A, IB = 10mA
- fT = 100 MHz @ VCE = 2V, IE = 0A
- COBO = - pF @ VCB = - V

Features

Low VCE(sat)

Die Size (Unawn)

500µm X 500µm, 20 Mils X 20 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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